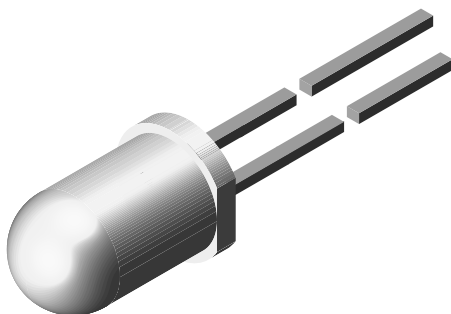




## High Speed Infrared Emitting Diode, 850 nm, Surface Emitter Technology



### DESCRIPTION

TSHG6410 is an infrared, 850 nm emitting diode based on surface emitter chip technology with high radiant power and high speed, molded in a clear, untinted plastic package.

### FEATURES

- Package type: leaded
- Package form: T-1 $\frac{3}{4}$
- Dimensions (in mm):  $\varnothing$  5
- Peak wavelength:  $\lambda_p = 850$  nm
- High reliability
- High radiant power
- High radiant intensity
- Angle of half intensity:  $\varphi = \pm 15^\circ$
- Low forward voltage
- Suitable for high pulse current operation
- Good spectral matching with Si photodetectors
- Material categorization: for definitions of compliance please see [www.vishay.com/doc?99912](http://www.vishay.com/doc?99912)



**RoHS**  
COMPLIANT  
HALOGEN  
**FREE**  
**GREEN**  
(5-2008)

### APPLICATIONS

- Infrared high speed remote control and free air data transmission systems with high modulation frequencies or high data transmission rate requirements
- Transmission systems according to IrDA requirements and for carrier frequency based systems (e.g. ASK/FSK - coded, 450 kHz or 1.3 MHz)

| PRODUCT SUMMARY |               |               |                  |            |
|-----------------|---------------|---------------|------------------|------------|
| COMPONENT       | $I_e$ (mW/sr) | $\varphi$ (°) | $\lambda_p$ (nm) | $t_r$ (ns) |
| TSHG6410        | 135           | $\pm 15$      | 850              | 10         |

#### Note

- Test conditions see table “Basic Characteristics”

| ORDERING INFORMATION |           |                              |                   |
|----------------------|-----------|------------------------------|-------------------|
| ORDERING CODE        | PACKAGING | REMARKS                      | PACKAGE FORM      |
| TSHG6410             | Bulk      | MOQ: 4000 pcs, 4000 pcs/bulk | T-1 $\frac{3}{4}$ |

#### Note

- MOQ: minimum order quantity

| ABSOLUTE MAXIMUM RATINGS ( $T_{amb} = 25$ °C, unless otherwise specified) |  |            |             |      |
|---|--|------------|-------------|------|
| PARAMETER   | TEST CONDITION                         | SYMBOL     | VALUE       | UNIT |
| Reverse voltage   |  | $V_R$      | 5           | V    |
| Forward current   |  | $I_F$      | 100         | mA   |
| Peak forward current  | $t_p/T = 0.5, t_p = 100$ $\mu$ s       | $I_{FM}$   | 200         | mA   |
| Surge forward current   | $t_p = 100$ $\mu$ s                    | $I_{FSM}$  | 1           | A    |
| Power dissipation   |  | $P_V$      | 180         | mW   |
| Junction temperature  |  | $T_j$      | 100         | °C   |
| Ambient temperature range   |  | $T_{amb}$  | -40 to +85  | °C   |
| Storage temperature range   |  | $T_{stg}$  | -40 to +100 | °C   |
| Soldering temperature   | $t \leq 5$ s, 2 mm from case           | $T_{sd}$   | 260         | °C   |
| Thermal resistance junction to ambient                                    | J-STD-051, leads 7 mm, soldered on PCB | $R_{thJA}$ | 230         | K/W  |

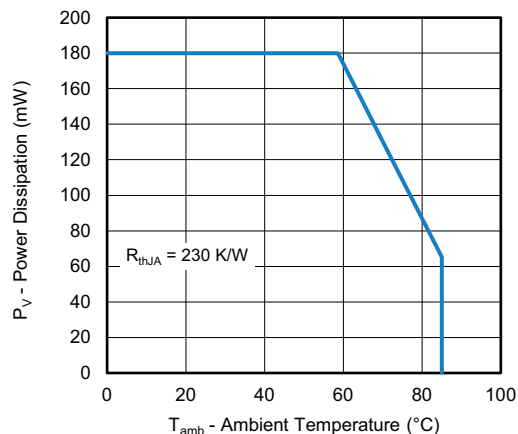


Fig. 1 - Power Dissipation Limit vs. Ambient Temperature

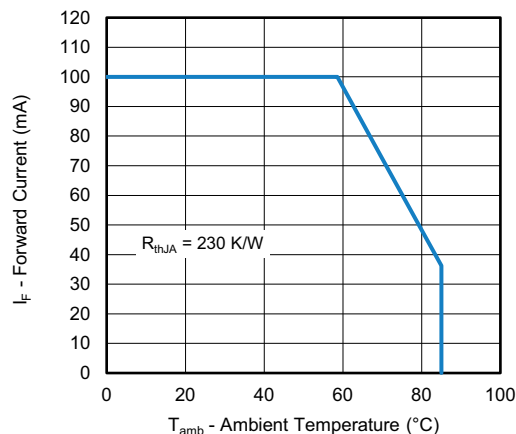


Fig. 2 - Forward Current Limit vs. Ambient Temperature

| BASIC CHARACTERISTICS (T <sub>amb</sub> = 25 °C, unless otherwise specified) |   |                             |                                    |       |      |       |
|--|---|-----------------------------|------------------------------------|-------|------|-------|
| PARAMETER  | TEST CONDITION                                  | SYMBOL                      | MIN.                               | TYP.  | MAX. | UNIT  |
| Forward voltage  | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | V <sub>F</sub>              | -                                  | 1.6   | 1.8  | V     |
|  | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs   | V <sub>F</sub>              | -                                  | 3.0   | -    | V     |
| Temperature coefficient of V <sub>F</sub>                                    | I <sub>F</sub> = 100 mA                         | TK <sub>V<sub>F</sub></sub> | -                                  | -1.5  | -    | mV/K  |
| Reverse current  |   | I <sub>R</sub>              | Not designed for reverse operation |       |      | μA    |
| Junction capacitance   | V <sub>R</sub> = 0 V, f = 1 MHz, E = 0          | C <sub>j</sub>              | -                                  | 53    | -    | pF    |
| Radiant intensity  | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | I <sub>e</sub>              | 35                                 | 135   | 220  | mW/sr |
|  | I <sub>F</sub> = 1 A, t <sub>p</sub> = 100 μs   | I <sub>e</sub>              | -                                  | 1230  | -    | mW/sr |
| Radiant power  | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | φ <sub>e</sub>              | -                                  | 61    | -    | mW    |
| Temperature coefficient of φ <sub>e</sub>                                    | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | TKφ <sub>e</sub>            | -                                  | -0.27 | -    | %/K   |
| Angle of half intensity  |   | φ                           | -                                  | ± 15  | -    | °     |
| Peak wavelength  | I <sub>F</sub> = 100 mA                         | λ <sub>p</sub>              | -                                  | 850   | -    | nm    |
| Spectral bandwidth   | I <sub>F</sub> = 100 mA                         | Δλ                          | -                                  | 30    | -    | nm    |
| Temperature coefficient of λ <sub>p</sub>                                    | I <sub>F</sub> = 100 mA, t <sub>p</sub> = 20 ms | TKλ <sub>p</sub>            | -                                  | 0.24  | -    | nm/K  |
| Rise time  | I <sub>F</sub> = 100 mA                         | t <sub>r</sub>              | -                                  | 10    | -    | ns    |
| Fall time  | I <sub>F</sub> = 100 mA                         | t <sub>f</sub>              | -                                  | 10    | -    | ns    |



**BASIC CHARACTERISTICS** ( $T_{amb} = 25\text{ }^{\circ}\text{C}$ , unless otherwise specified)

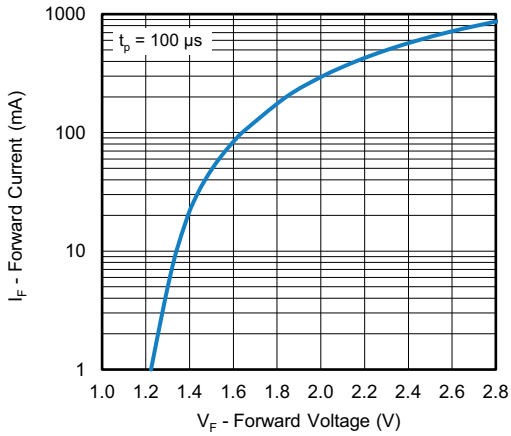


Fig. 3 - Forward Current vs. Forward Voltage

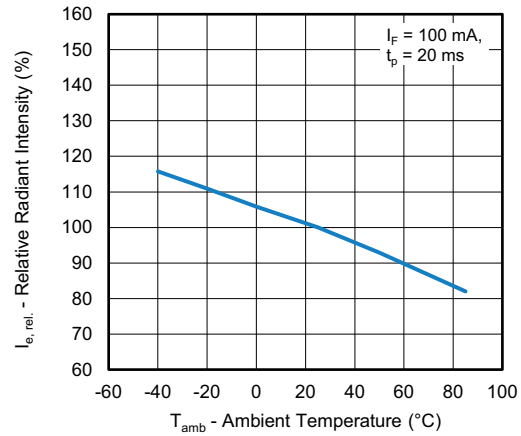


Fig. 6 - Relative Radiant Intensity vs. Ambient Temperature

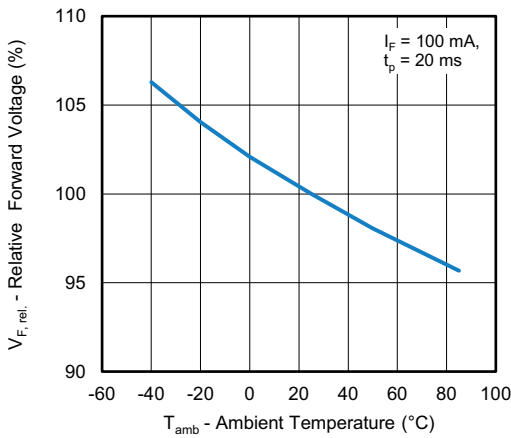


Fig. 4 - Relative Forward Voltage vs. Ambient Temperature

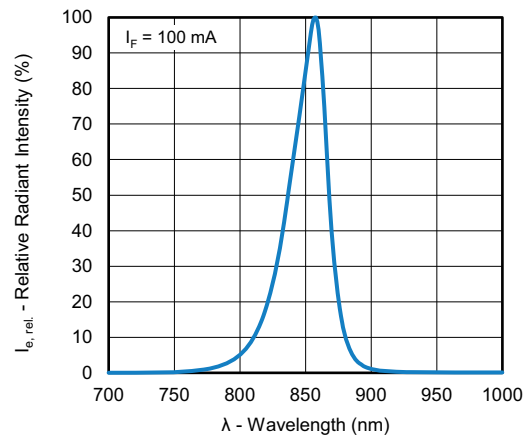


Fig. 7 - Relative Radiant Intensity vs. Wavelength

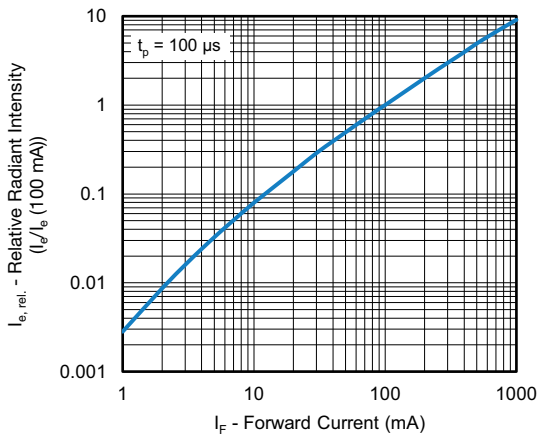


Fig. 5 - Relative Radiant Intensity vs. Forward Current

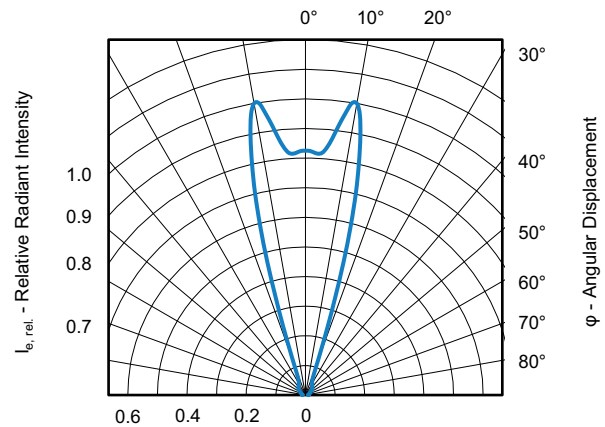


Fig. 8 - Relative Radiant Intensity vs. Angular Displacement





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